

SMALL SIGNAL PNP TRANSISTOR

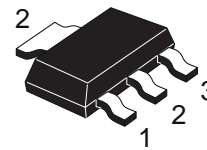
PRELIMINARY DATA

Type	Marking
BF721	721

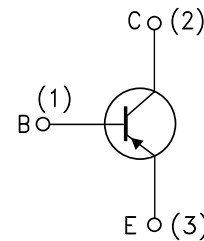
- SILICON EPITAXIAL PLANAR PNP HIGH VOLTAGE TRANSISTOR
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS BF720

APPLICATIONS

- VIDEO AMPLIFIER CIRCUITS (RGB CATHODE CURRENT CONTROL)
- TELEPHONE WIRELINE INTERFACE (HOOK SWITCHES, DIALER CIRCUITS)


SOT-223

INTERNAL SCHEMATIC DIAGRAM



SC08810

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	-300	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-300	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_C	Collector Current	-100	mA
I_{CM}	Collector Peak Current	-200	mA
P_{tot}	Total Dissipation at $T_C = 25\text{ }^\circ\text{C}$	1.4	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$

BF721

THERMAL DATA

$R_{thj-amb}$ •	Thermal Resistance Junction-Ambient	Max	89.3	°C/W
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• Device mounted on a PCB area of 1 cm²

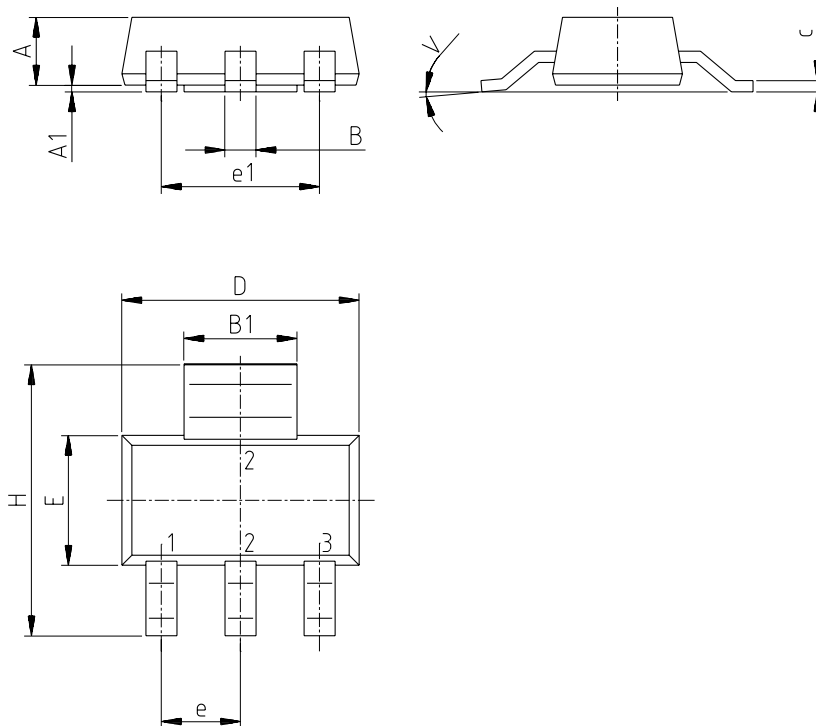
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = -200 V V _{CB} = -200 V V _{CB} = -300 V			-10 -10 -100	nA μA μA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = -5 V			-50	nA
V _{(BR)CEO} *	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -10 mA	-300			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -100 μA	-5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = -30 mA I _B = -5 mA			-0.6	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = -30 mA I _B = -5 mA			-1.2	V
h _{FE} *	DC Current Gain	I _C = -25 mA V _{CE} = -20 V	50			
f _T	Transition Frequency	I _C = -15 mA V _{CE} = -10V f = 100 MHz	60			MHz
C _{CB0}	Collector-Base Capacitance	I _E = 0 V _{CB} = -10 V f = 1MHz		6		pF
C _{EBO}	Emitter-Base Capacitance	I _C = 0 V _{EB} = -2 V f = 1MHz		22		pF

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



P008B

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